

Datasheet

M.2 (S80) 3TG6-P series

- SATA III solution for industrial field
- High IOPS
- Excellent random performance
- End to end data path protection
- iData Guard for abnormal power failure
- iCell technology for data protection (optional)
- Compatible with M.2 2280-D2-B-M standard



Introduction

Innodisk M.2 (S80) 3TG6-P is SATA III 6Gb/s solid state disk, which delivers excellent performance, especially in random data transfer rate, and which offers reliability making it the ideal solution for a variety of applications, including embedded system, industrial computing, and enterprise field. M.2 (S80) 3TG6-P not only performs unmatched performance, but also designed with Innodisk owned technical knowhow to ensure the data integrity and highest levels of reliability.

Innodisk M.2 (S80) 3TG6-P is designed for industrial field, and supports several standard features, including TRIM, NCQ, and S.M.A.R.T. In addition, Innodisk's exclusive industrial-oriented firmware provides a flexible customization service, making it perfect for a variety of industrial applications.

M.2 (S80) 3TG6-P series

Diagram

**Contact us for more information
about the M.2 (S80) 3TG6-P.**

Innodisk is a service-driven provider of industrial embedded flash and DRAM storage products and technologies, with a focus on the cloud computing, industrial/embedded, and aerospace and defense industries.

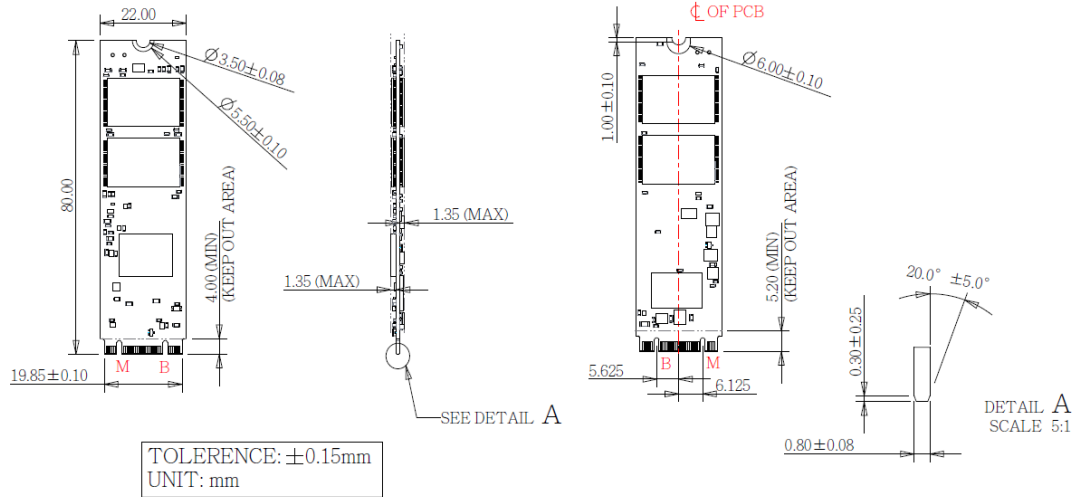
Headquarters (Taiwan)

5F., No. 237, Sec. 1, Datong Rd., Xizhi
Dist., New Taipei City 221, Taiwan
Tel: +886-2-7703-3000
Email: sales@innodisk.com

Branch Offices:

USA
usasales@innodisk.com
+1-510-770-9421
Europe
eusales@innodisk.com
+31-40-3045-400
Japan
jpsales@innodisk.com
+81-3-6667-0161
China
sales_cn@innodisk.com
+86-755-21673689
www.innodisk.com

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Specifications

| | |
|-------------------------------|---|
| Interface | SATA III |
| Flash Type | 3D TLC |
| P/E cycle | 3,000 |
| Capacity | 128GB~2TB |
| Max. Channels | 4 |
| Sequential R/W (MB/sec, max.) | 510/400 |
| Max. Power Consumption | 2.9W(878mA x 3.3V) |
| Thermal Sensor | ✓ |
| External DRAM buffer | ✓ |
| H/W Write Protect | Optional |
| ATA Security | ✓ |
| S.M.A.R.T. | ✓ |
| Dimension (WxLxH) | 22.0 X 80.0 X 3.8mm (Max) |
| Environment | Vibration: 20G @7~2000Hz Shock: 1500G @ 0.5ms Storage Temperature: -40°C ~ +85°C MTBF: 3 million hours |

Ordering Information

| Operation Temp. | 128GB | 256GB | 512GB | 1TB | 2TB |
|-------------------------------------|----------------------|----------------------|----------------------|-----------------------|--------------------|
| Standard Grade (0°C ~ +70°C) | DGM28-A28M71%C*DL(S) | DGM28-B56M71%C*QL(S) | DGM28-C12M71%C*QL(S) | DGM28-01TM71%C*Q**(S) | DGM28-02TM71%C*Q** |
| Industrial Grade (-40°C ~ +85°C) | DGM28-A28M71GW*DL(S) | DGM28-B56M71GW*QL(S) | DGM28-C12M71GW*QL(S) | DGM28-01TM71GWAQ**(S) | DGM28-02TM71GWAQQ |

%. G: 96 layers 3D TLC; K: 112 layers 3D TLC

*, 1/2/A: PCB version **, L/Q: Flash config. S: Single-sided

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